

**FEATURES**

- Circular Active Area
- Ideal for EUV Detection
- Higher Overall Responsivity
- Lower Noise
- Superior Radiation Hardness
- High Photon Flux Robustness
- TO-8 package

**Electro-Optical Characteristics at 25°C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ5.01 mm		20		mm <sup>2</sup>
Responsivity	(see graph on next page)				A/W
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 μA	5	10		Volts
Capacitance, C	V <sub>R</sub> = 0 V		1.55	3	nF
Rise Time	R <sub>L</sub> = 50 Ω, V <sub>R</sub> = 0 V		2		usec
Shunt Resistance	V <sub>f</sub> = ±10 mV	50	200		MOhms

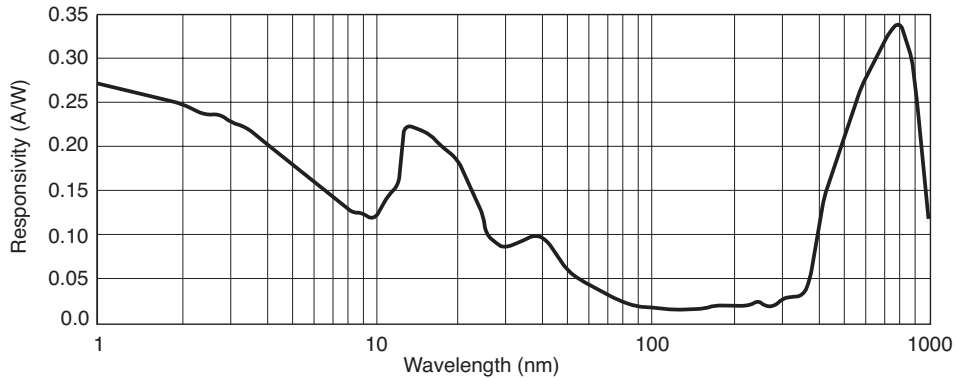
<sup>1</sup> Die Active Area = Φ5.5 mm, Aperture Size = Φ4.9 mm.

**Thermal Parameters**

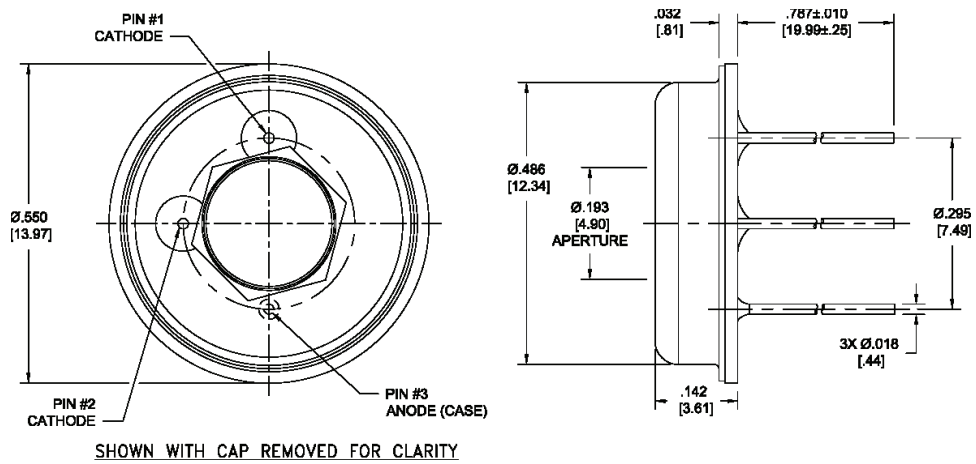
Parameters	Units
Storage Temperature Range	-20°C to 100°C
Operating Temperature Range	-20°C to 80°C
Maximum Junction Temperature	100°C
Lead Soldering Temperature <sup>2</sup>	260°C

<sup>2</sup> 1/16" from case for 10 seconds.

**Typical Photon Responsivity**



**Package Information**



Dimensions are in inches [metric] units.

Specifications are subject to change without prior notice.